

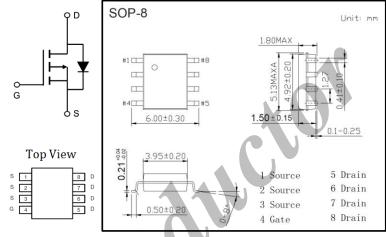
30V P-Channel Enhancement Mode MOSFET

• General Description

AP4411 combines advanced MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is most suitable to load-switch or PWM applications.

Applications

- DC-DC converter for portable devices
- Load switch





• Product Summary

Vds	-30V
In (at $V_{GS} = -10V$)	-8A
$R_{DS(ON)}$ (at $V_{GS} = -10V$)	< 32mΩ
RDS(ON) (at $V_{GS} = -4.5V$)	< 55mΩ

• Absolute Maximum Ratings Ta = 25°C

Parameter	<u> </u>	Symbol	Rating	Unit		
Drain-Source Voltage		V_{DS}	-30	V		
Gate-Source Voltage		V_{GS}	±20	V		
Continuous Drain Current	Ta = 25°C	I_{D}	-8	۸		
Continuous Drain Current	Ta = 70°C	1D	-6.6			
Pulsed Drain Current	I_{DM}	-40	_ A			
Avalanche Current	I _{AS} , I _{AR}	23				
Avalanche Energy (L = 0.1mH)		Eas, Ear	26	mJ		
Power Dissipation	Ta = 25°C	P_D	3.1	- W		
	Ta = 70°C		2			
Junction and Storage Temperature Range	T_J , T_{STG}	-55 to 150	°C			
Thermal Characteristics						
Thermal Resistance. Junction-to-Ambient	t ≤ 10s	$R_{ heta JA}$	40			
	Steady State	NθJA	75	°C/W		
Thermal Resistance. Junction-to-Lead	Steady State	$R_{ heta JL}$	24			



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• Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Parameters					_		
Drain-Source Breakdown Voltage	V_{DSS}	I _D =-250μA, V _{GS} =0V	-30			V	
Zero Gate Voltage Drain Current	T	V_{DS} =-30V, V_{GS} =0V			-1	μА	
	I_{DSS}	V_{DS} =-30V, V_{GS} =0V, T_{J} =55°C		K	-5		
Gate-Body Leakage Current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=-250\mu A$	-1.3	-1.85	-2.4	V	
On-State Drain Current	$I_{D(ON)}$	V_{GS} =-10V, V_{DS} =-5V	-40			A	
		V _{GS} =-10V, I _D =-8A	4 1	21	32		
Static Drain-Source On-Resistance	R _{DS(ON)}	V_{GS} =-10V, I_{D} =-8A, T_{J} =125°C		31.5	38	mΩ	
		V_{GS} =-4.5V, I_D =-5A	V	33	55		
Forward Transconductance	$\mathbf{g}_{ ext{FS}}$	V_{DS} =-5V, I_D =-8A		19		S	
Diode Forward Voltage	V_{SD}	$I_S=-1A$, $V_{GS}=0V$		-0.8	-1	V	
Maximum Body-Diode Continuous Current	I_S				-3.5	Α	
Dynamic Parameters							
Input Capacitance	C_{iss}			760			
Output Capacitance	C_{oss}	V_{GS} =0V, V_{DS} =-15V, f=1MHz		140		pF	
Reverse Transfer Capacitance	C_{rss}			95			
Gate Resistance	Rg	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.5	3.2	5	Ω	
Switching Parameters							
Total Gate Charge (10V)				13.6	16		
Total Gate Charge (4.5V)	Qg	V - 10V V - 15V I - 0A		6.7	8	nC	
Gate Source Charge	Q_{gs}	V_{GS} =-10V, V_{DS} =-15V, I_{D} =-8A		2.5			
Gate Drain Charge	Q_{gd}			3.2			
Turn-On Delay Time	t _{D(on)}			8			
Turn-On Rise Time	t_{r}	V_{GS} =-10V, V_{DS} =-15V, R_{L} =1.8 Ω ,		6		ns	
Turn-Off Delay Time	$t_{D(off)}$	$R_{GEN}=3\Omega$		17			
Turn-Off Fall Time	t_{f}			5			
Body Diode Reverse Recovery Time	t _{rr}	I_F =-8A, d_i/d_t =100A/ μ s		15			
Body Diode Reverse Recovery Charge	Q_{rr}	I_F =-8A, d_i/d_t =100A/ μ s		9.7		nC	

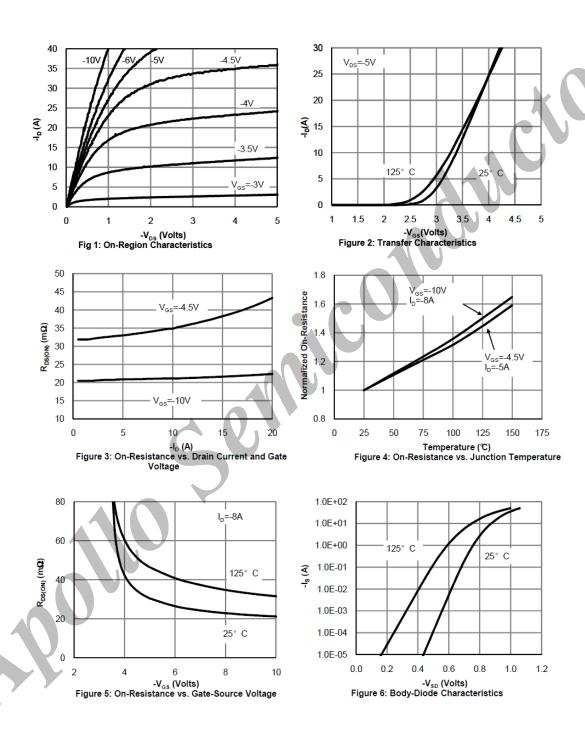
Ordering Information

Ordering Part Number	Package	MOQ
AP4411	SOP-8	2,500 pcs / reel

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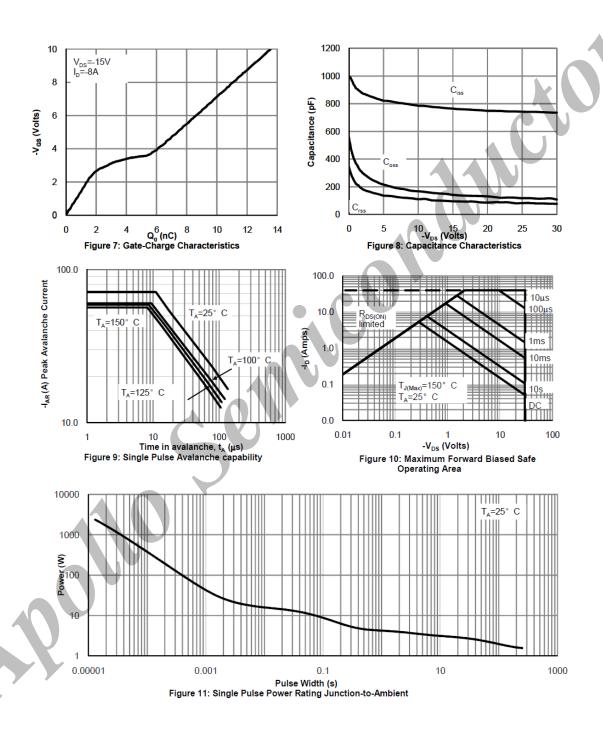
• Typical Electrical and Thermal Characteristics



Note 1: The static characteristics in Figure 1 to 6 are obtained using $<300\mu A$ pulses, duty cycle 0.5% max.



• Typical Electrical and Thermal Characteristics



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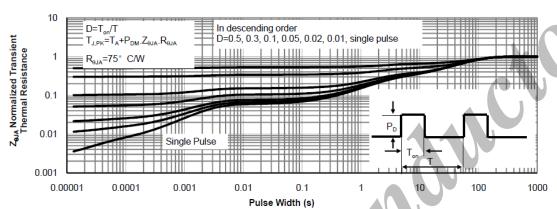


Figure 12: Normalized Maximum Transient Thermal Impedance

Note 2: The curves in Figure 10 to 12 are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in^2 FR-4 board with 2oz. copper, assuming a maximum junction temperature of $T_{\text{J}(\text{MAX})}$ =150°C. The SOA curve provides a single pulse rating.



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